



# Silicon NPN Power Transistor



TO-3P Leaded Plastic Package RoHS compliant



## **DESCRIPTION:**

- 1. Collector Current : I<sub>C</sub>= 10A
- Collector-Emitter Breakdown Voltage:- V<sub>(BR)CEO</sub> = 45V(Min)- BD245;
  60V(Min)- BD245A 80V(Min)- BD245B; 100V(Min)- BD245C
- 3. Complement to Type **BD246/A/B/C**

## **APPLICATIONS:**

Designed for use in general purpose power amplifier and switching applications

### ABSOLUTE MAXIMUM RATINGS ( $T_a = 25 \circ C$ )

DESCRIPTION	SYMBOL	VALUE	UNIT		
Collector-Emitter Voltage (R <sub>BE</sub> = 100Ω)	BD245		55		
	BD245A	V <sub>CER</sub>	70	V	
	BD245B		90	v	
	BD245C		115		
Collector-Emitter Voltage	BD245	V <sub>CEO</sub>	45		
	BD245A		60	V	
	BD245B		80	•	
	BD245C		100		
Emitter-Base Voltage		V <sub>EBO</sub>	5	V	
Collector Current-Continuous	Ι <sub>C</sub>	10			
Collector Current-Peak	I <sub>CM</sub>	15	A		
Base Current	I <sub>B</sub>	3			
Collector Power Dissipation	@ T <sub>a</sub> =25°C	P <sub>c</sub>	3	W	
	@ T <sub>c</sub> =25°C		80		
Junction Temperature		TJ	150	°C	
Storage Temperature Range		T <sub>stg</sub>	-65~150	-U	
THERMAL CHARACTERISTICS:					
DESCRIPTION		SYMBOL	VALUE (Max)	UNIT	
Thermal Resistance, Junction to Case		$R_{\theta  j\text{-}c}$	1.56	°C/W	
		,	•		





DESCRIPTION		SYMBOL	TEST CONDITIONS	VALUES			UNIT	
			TEST CONDITIONS	MIN	Тур.	MAX	UNII	
Collector-Emitter Breakdown Voltage	BD245 BD245A BD245B BD245C	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 30mA ;I <sub>B</sub> =0	45 60 80 100	  	  		
Collector-Emitter Saturation Voltage		V <sub>CE(sat)-1</sub>	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.3A			1.0	V	
		V <sub>CE(sat)-2</sub>	I <sub>C</sub> = 10A; I <sub>B</sub> = 2.5A			4.0		
Base-Emitter On Voltage		V <sub>BE(on)-1</sub>	I <sub>C</sub> = 3A ; V <sub>CE</sub> = 4V			1.6		
Base Emilier on Vollage		$V_{BE(on)-2}$	I <sub>C</sub> = 10A ; V <sub>CE</sub> = 4V			3.0		
	BD245	I <sub>CES</sub>	V <sub>CE</sub> = 55V; V <sub>BE</sub> = 0			0.4	mA	
Collector Cutoff Current	BD245A		V <sub>CE</sub> = 70V; V <sub>BE</sub> = 0					
	BD245B		V <sub>CE</sub> = 90V; VBE= 0					
	BD245C		V <sub>CE</sub> = 115V; V <sub>BE</sub> = 0					
Collector Cutoff Current	BD245/A	I <sub>CEO</sub>	$V_{CE}$ = 30V;IB= 0			0.7		
BD245B/C		-	$V_{CE} = 60V; I_B = 0$			1		
Emitter Cutoff Current		I <sub>EBO</sub>	V <sub>EB</sub> = 5V; I <sub>C</sub> =0			I		
DC Current Gain		h <sub>FE-1</sub>	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 4V	40				
		h <sub>FE-2</sub>	I <sub>C</sub> = 3A ; V <sub>CE</sub> = 4V	20				
		h <sub>FE-3</sub>	I <sub>C</sub> = 10A ; V <sub>CE</sub> = 4V	4				
Current-Gain—Bandwidth Product		f <sub>T</sub>	I <sub>C</sub> = 0.5A ;V <sub>CE</sub> = 10V,f <sub>test</sub> = 1.0MHz	3.0			MHz	
Switching times			•	-	-			
Turn-on Time		t <sub>on</sub>	$I_{C} = 1A; I_{B1} = -I_{B2} = 0.1A;$		0.2		μs	
Turn-off Time		t <sub>off</sub>	R <sub>L</sub> =20Ω; V <sub>BE(OFF)</sub> = -3.7V		0.8		μs	

# FLECTRICAL CHARACTERISTICS at T = 25 °C





# **Typical Characteristic Curves**

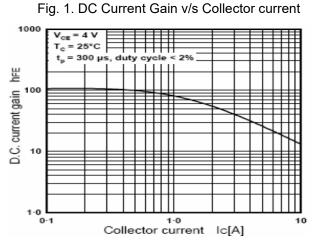
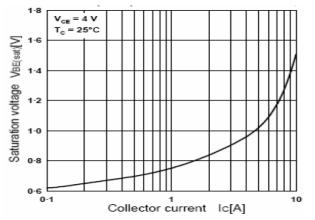
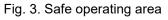
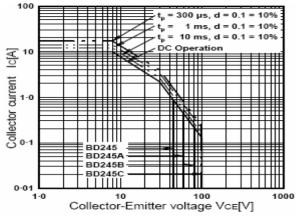


Fig. 2. Saturation voltage v/s Collector current







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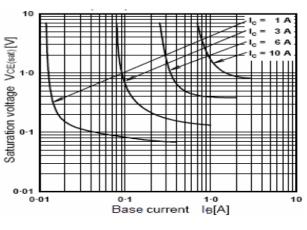
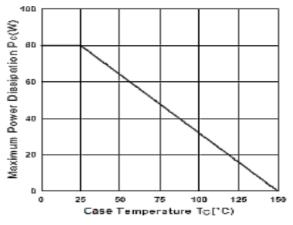


Fig. 4. Saturation voltage v/s Base current

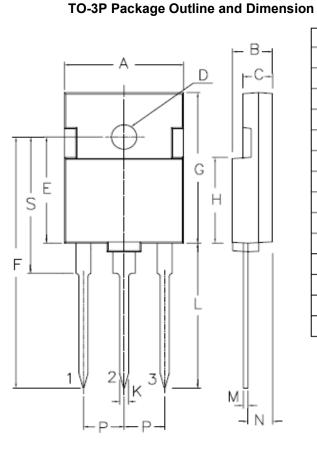








# **Package Details**



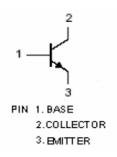
#### DIM MIN. MAX. А 15.8 16.4 5.2 5.7 В 3.8 4.2 С ø3.3 D ø3.6 E 14.50 15.10 F 33.25 36.75 G 21.25 20.75 Н 12.25 11.50 Κ 1.0 1.30 L 18.75 21.65 0.40 М 0.60 3.45 Ν 3.15 Ρ 5.21 5.72 S 18.75 19.25

1. BASE

2. COLLECTOR

3. EMITTER

**Pin Configuration:** 



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PIN CONFIGURATION





# Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- · Temperature 5 °C to 30 °C
- · Humidity between 40 to 70 %RH
- · Air should be clean.
- · Avoid harmful gas or dust.
- $\cdot\,$  Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- · Avoid rapid change of temperature.
- · Avoid condensation.
- $\cdot\,$  Mechanical stress such as vibration and impact shall be avoided.
- $\cdot\,$  The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

### Shelf Life of CDIL Products

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

### Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start. For this, the following JEDEC table may be referred:

JEDEC MSL Level				
Level	Time	Condition		
1	Unlimited	≤30 °C / 85% RH		
2	1 Year	≤30 °C / 60% RH		
2a	4 Weeks	≤30 °C / 60% RH		
3	168 Hours	≤30 °C / 60% RH		
4	72 Hours	≤30 °C / 60% RH		
5	48 Hours	≤30 °C / 60% RH		
5a	24 Hours	≤30 °C / 60% RH		
6	Time on Label(TOL)	≤30 °C / 60% RH		





## **Customer Notes**

### **Component Disposal Instructions**

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

### Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



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